650V N-Channel MOSFETS

PJX53N65D

General Description

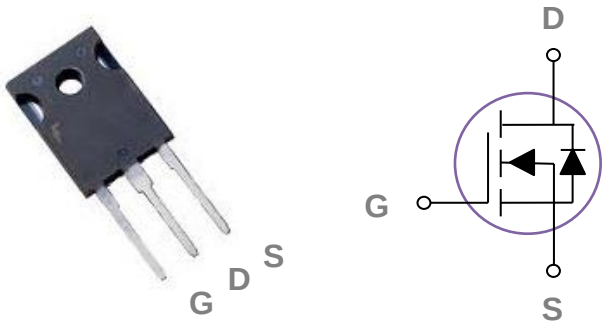
These N-Channel enhancement mode power field effect transistors are using Super Junction technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switch mode power supply

BVDSS	RDSON	ID
650V	69mΩ	53A

Features

- *53A,650V, RDS(ON) =69mΩ@VGS = 10V*
- *Improved dv/dt capability*
- *Fast switching*
- *100% EAS Guaranteed*
- *Green Device Available*

TO247 Pin Configuration



Applications

- *High efficient switched mode power supplies*
- *LED Lighting*
- *Adapter/charger*

Absolute Maximum Ratings (Tc=25℃ unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	650	V
V_{GS}	Gate-Source Voltage	±30	V
I_D	Drain Current – Continuous (T_C=25˚C)	53	A
	Drain Current – Continuous (T_C=100˚C)	33.5	A
I_{DM}	Drain Current – Pulsed[1]	212	A
EAS	Single Pulse Avalanche Energy[2]	344	mJ
IAS	Single Pulse Avalanche Current[2]	8.3	A
P_D	Power Dissipation (T_C=25˚C)	390	W
	Power Dissipation – Derate above 25˚C	3.125	W/˚C
T_{STG}	Storage Temperature Range	-55 to 150	˚C
T_J	Operating Junction Temperature Range	-55 to 150	˚C

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	62	˚C/W
$R_{\theta JC}$	Thermal Resistance Junction to Case	---	0.32	˚C/W

Electrical Characteristics (T_J=25 ˚C, unless otherwise noted)

Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=1mA	650	---	---	V
$\triangle BV_{DSS}/\triangle T_J$	BV_{DSS} Temperature Coefficient	Reference to 25˚C , I_D=1mA	---	0.48	---	V/˚C
I_{DSS}	Drain-Source Leakage Current	V_{DS}=650V , V_{GS}=0V , T_J=25˚C	---	---	10	uA
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±30V , V_{DS}=0V	---	---	±100	nA

On Characteristics

$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V , I_D=26.5A	---	55	69	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =1mA	2	---	4	V
$\triangle V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-8.83	---	mV/˚C

Dynamic and switching Characteristics

Q_g	Total Gate Charge[2,3]	V_{DS}=400V , V_{GS}=10V , I_D=30A	---	60.2	---	nC
Q_{gs}	Gate-Source Charge[2,3]		---	24.5	---	
Q_{gd}	Gate-Drain Charge[2,3]		---	18.7	---	
$T_{d(on)}$	Turn-On Delay Time[2,3]	V_{DD}=400V , V_{GS}=10V , R_G=25Ω I_D=30A	---	129	---	ns
T_r	Rise Time[2,3]		---	150	---	
$T_{d(off)}$	Turn-Off Delay Time[2,3]		---	100	---	
T_f	Fall Time[2,3]		---	77	---	
C_{iss}	Input Capacitance	V_{DS}=50V , V_{GS}=0V , F=100KHz	---	4650	---	pF
C_{oss}	Output Capacitance		---	280	---	
C_{rss}	Reverse Transfer Capacitance		---	8.6	---	

Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	V_G=V_D=0V , Force Current	---	---	53	A
I_{SM}	Pulsed Source Current		---	---	106	A
V_{SD}	Diode Forward Voltage	V_{GS}=0V , I_S=53A , T_J=25˚C	---	---	1.4	V
t_{rr}	Reverse Recovery Time[2]	V_{GS}=0V,I_S=30A , dI/dt=100A/μs , T_J=25˚C	---	174	---	ns
Q_{rr}	Reverse Recovery Charge[2]		---	1.05	---	uC
Irrm	Peak reverse recovery current		---	11.32	---	A

Note :
1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. V_{DD}=100V,V_{GS}=10V,L=10mH,I_{AS}=8.3A.,R_G=25Ω, Starting T_J=25˚C.
3. The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%.
4. Essentially independent of operating temperature.

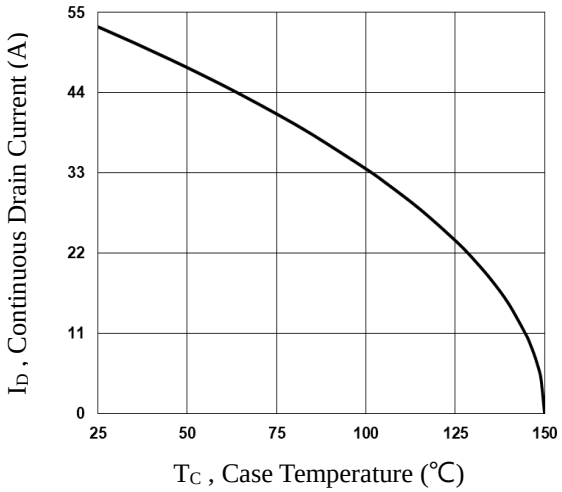


Fig.1 Continuous Drain Current vs. T_C

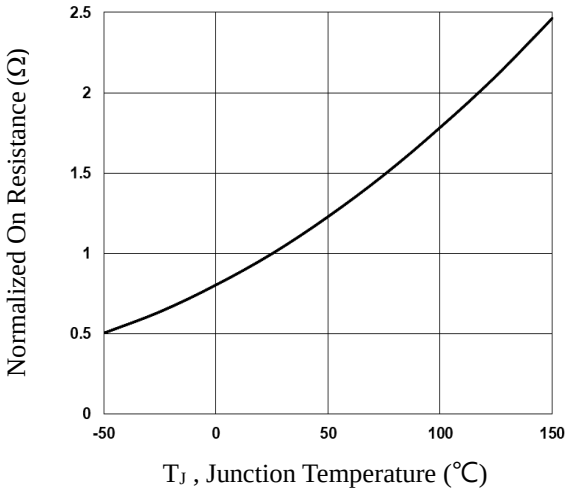


Fig.2 Normalized RDSON vs. T_J

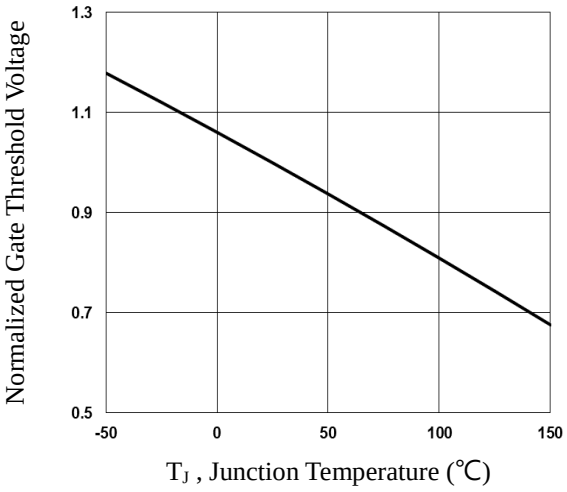


Fig.3 Normalized V_{th} vs. T_J

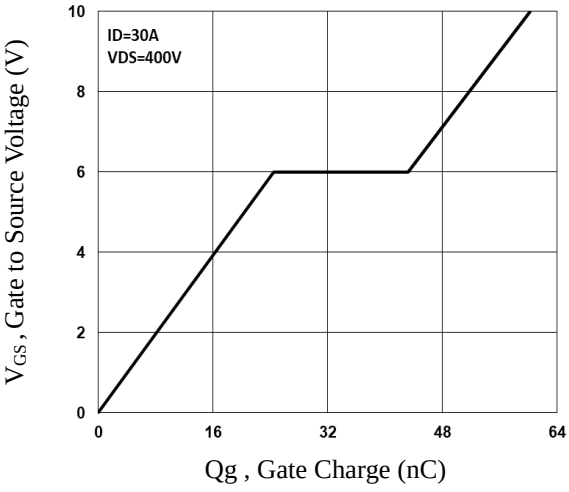


Fig.4 Gate Charge Waveform

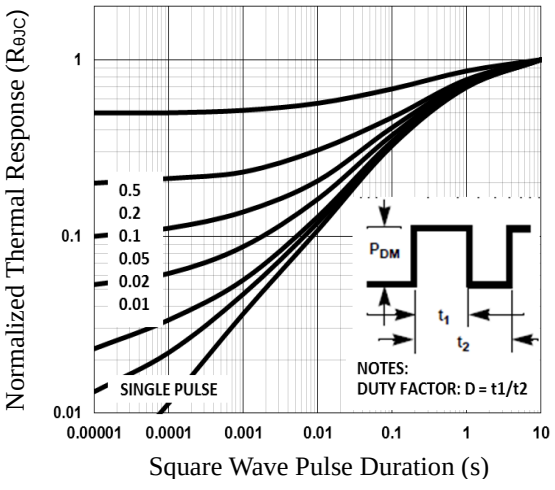


Fig.5 Normalized Transient Impedance

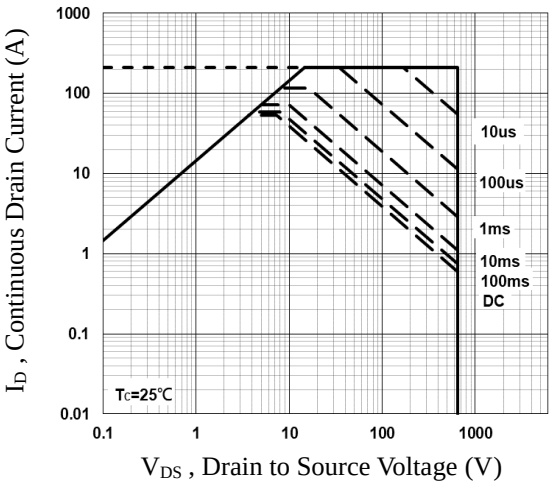


Fig.6 Maximum Safe Operation Area

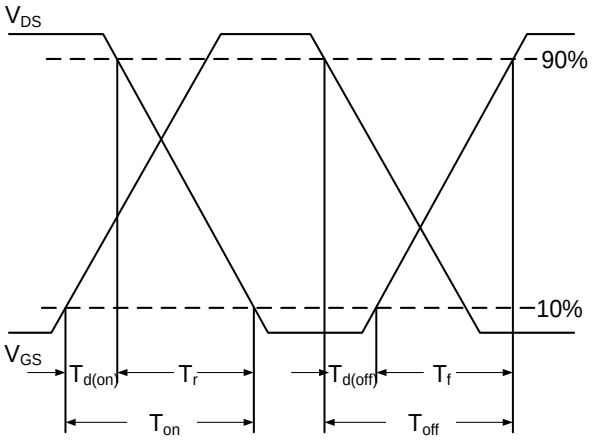


Fig.7 Switching Time Waveform

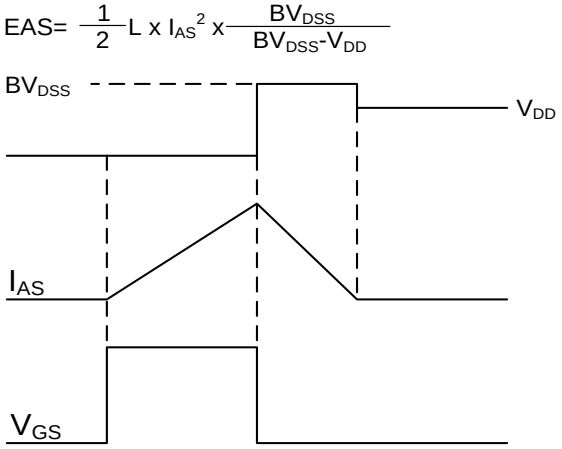
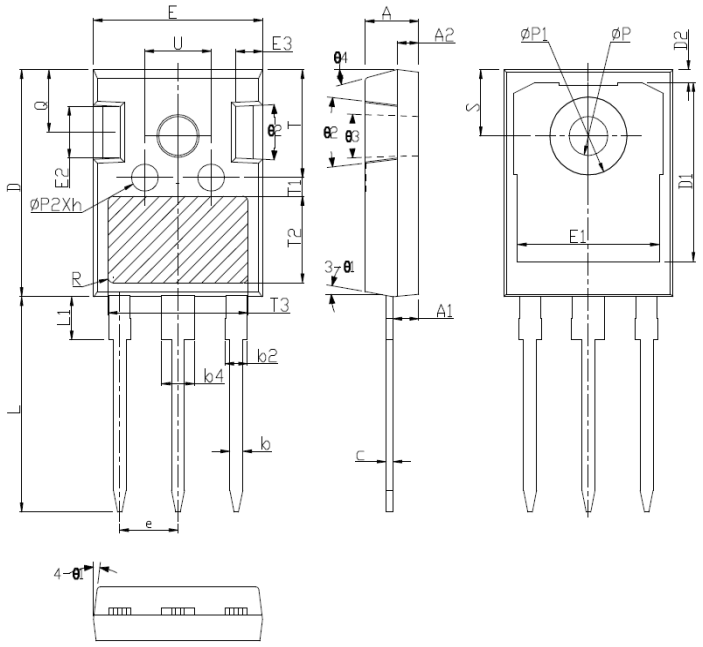


Fig.8 EAS Waveform

TO247 PACKAGE INFORMATION



Symbol	Dimensions In Millimeters			Symbol	Dimensions In Millimeters		
	Min	Nom	Max		Min	Nom	Max
A	4.750	5.000	5.250	L	19.520	19.920	20.320
A1	2.160	2.410	2.660	L1	---	---	4.300
A2	1.850	2.000	2.150	ΦP	3.350	3.600	3.850
b	1.110	1.200	1.350	ΦP1	---	---	7.300
b2	1.900	2.010	2.250	ΦP2	2.250	2.500	2.750
b4	2.900	3.100	3.250	Q	5.500	5.800	6.100
c	0.510	0.610	0.750	S	6.15BSC		
D	20.600	21.000	21.400	R	0.50REF		
D1	16.150	16.550	16.950	T	9.700	---	10.300
D2	1.000	1.200	1.400	T1	1.65REF		
E	15.500	15.800	16.100	T2	8.00REF		
E1	13.000	13.300	13.600	T3	12.80REF		
E2	4.700	5.000	5.300	U	5.900	---	6.500
E3	2.250	2.500	2.750	θ1	3°	7°	10°
e	5.44BSC			θ2	2°	5°	8°
h	0.000	0.100	0.250	θ3	1°	---	2°
				θ4	10°	15°	20°